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Kind regards,

Team Nexperia

PDTA144E series

PNP resistor-equipped transistors; R1 = 47 k Ω , R2 = 47 k Ω

Rev. 8 — 14 November 2011

Product data sheet

1. Product profile

1.1 General description

PNP Resistor-Equipped Transistor (RET) family in Surface-Mounted Device (SMD) plastic packages.

Table 1. Product overview

Type number	Package	ackage		NPN	Package	
	NXP	JEITA	JEDEC	complement	configuration	
PDTA144EE	SOT416	SC-75	-	PDTC144EE	ultra small	
PDTA144EM	SOT883	SC-101	-	PDTC144EM	leadless ultra small	
PDTA144ET	SOT23	-	TO-236AB	PDTC144ET	small	
PDTA144EU	SOT323	SC-70	-	PDTC144EU	very small	

1.2 Features and benefits

- 100 mA output current capability
- Built-in bias resistors
- Simplifies circuit design
- Reduces component count
- Reduces pick and place costs
- AEC-Q101 qualified

1.3 Applications

- Digital applications in automotive and industrial segments
- Control of IC inputs

- Cost-saving alternative for BC847/857 series in digital applications
- Switching loads

1.4 Quick reference data

Table 2. Quick reference data

Parameter	Conditions	Min	Тур	Max	Unit
collector-emitter voltage	open base	-	-	-50	V
output current		-	-	-100	mA
bias resistor 1 (input)		33	47	61	kΩ
bias resistor ratio		8.0	1	1.2	
	collector-emitter voltage output current bias resistor 1 (input)	collector-emitter voltage open base output current bias resistor 1 (input)	collector-emitter voltage open base - output current - bias resistor 1 (input) 33	collector-emitter voltage open base output current bias resistor 1 (input) 33 47	collector-emitter voltage open base50 output current100 bias resistor 1 (input) 33 47 61



2. Pinning information

Table 3. **Pinning** Simplified outline **Graphic symbol** Pin Description SOT23; SOT323; SOT416 1 input (base) 3 2 GND (emitter) 3 output (collector) 2 006aaa144 sym003 **SOT883** 1 input (base) 2 GND (emitter) output (collector) Transparent

3. Ordering information

Table 4. Ordering information

Type number	Package						
71	Name	Description	Version				
PDTA144EE	SC-75	plastic surface-mounted package; 3 leads	SOT416				
PDTA144EM	SC-101	leadless ultra small plastic package; 3 solder lands; body 1.0 \times 0.6 \times 0.5 mm	SOT883				
PDTA144ET	-	plastic surface-mounted package; 3 leads	SOT23				
PDTA144EU	SC-70	plastic surface-mounted package; 3 leads	SOT323				

4. Marking

Table 5. Marking codes

Marking code ^[1]
07
DR
*07
*07

[1] * = placeholder for manufacturing site code

5. Limiting values

Table 6. Limiting values

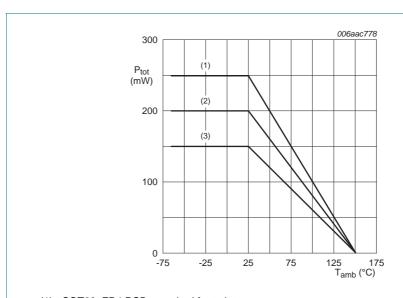
In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{CBO}	collector-base voltage	open emitter	-	-50	V
V_{CEO}	collector-emitter voltage	open base	-	-50	V
V_{EBO}	emitter-base voltage	open collector	-	-10	V
VI	input voltage				
	positive		-	+10	V
	negative		-	-40	V
I _O	output current		-	-100	mA
I _{CM}	peak collector current	single pulse; $t_p \le 1 \text{ ms}$	-	-100	mA
P _{tot}	total power dissipation	$T_{amb} \le 25 ^{\circ}C$			
	PDTA144EE (SOT416)		[1][2]	150	mW
	PDTA144EM (SOT883)		[2][3]	250	mW
	PDTA144ET (SOT23)		<u>[1]</u> -	250	mW
	PDTA144EU (SOT323)		<u>[1]</u> -	200	mW
Tj	junction temperature		-	150	°C
T _{amb}	ambient temperature		-65	+150	°C
T _{stg}	storage temperature		-65	+150	°C

^[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

^[2] Reflow soldering is the only recommended soldering method.

^[3] Device mounted on an FR4 PCB with 70 μm copper strip line, standard footprint.



- (1) SOT23; FR4 PCB, standard footprint SOT883; FR4 PCB with 70 μm copper strip line, standard footprint
- (2) SOT323; FR4 PCB, standard footprint
- (3) SOT416; FR4 PCB, standard footprint

Fig 1. Power derating curves

6. Thermal characteristics

Table 7. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air				
	PDTA144EE (SOT416)		[1][2]	-	830	K/W
	PDTA144EM (SOT883)		[2][3]	-	500	K/W
	PDTA144ET (SOT23)		[1] -	-	500	K/W
	PDTA144EU (SOT323)		<u>[1]</u> _	-	625	K/W

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Reflow soldering is the only recommended soldering method.
- [3] Device mounted on an FR4 PCB with 70 μm copper strip line, standard footprint.

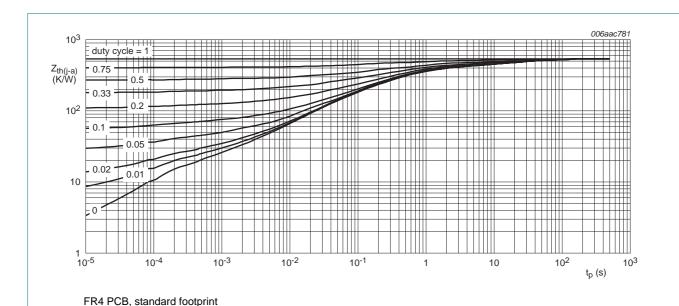


Fig 2. Transient thermal impedance from junction to ambient as a function of pulse duration for PDTA144EE (SOT416); typical values

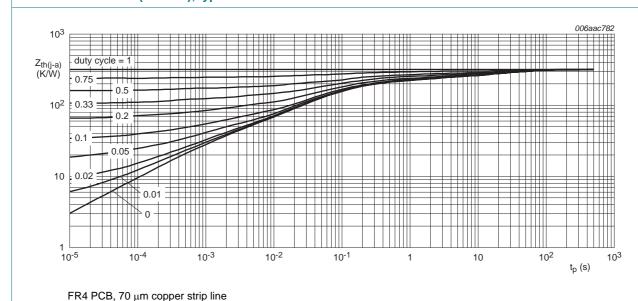


Fig 3. Transient thermal impedance from junction to ambient as a function of pulse duration for PDTA144EM (SOT883); typical values

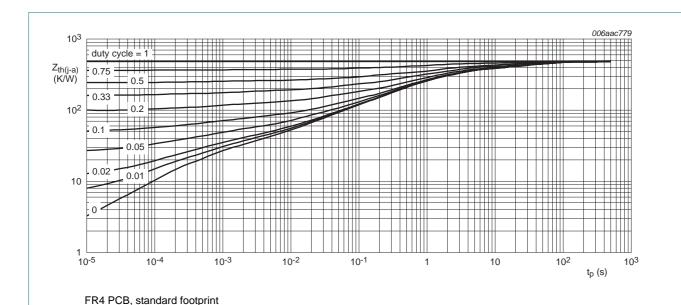


Fig 4. Transient thermal impedance from junction to ambient as a function of pulse duration for PDTA144ET (SOT23); typical values

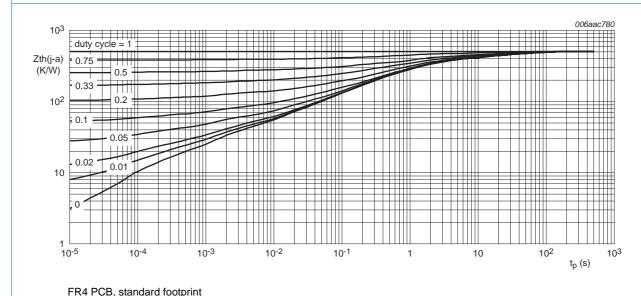


Fig 5. Transient thermal impedance from junction to ambient as a function of pulse duration for PDTA144EU (SOT323); typical values

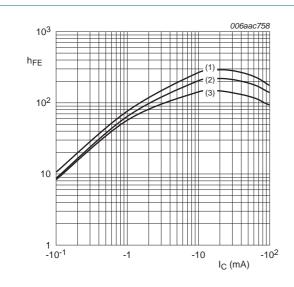
7. Characteristics

Table 8. Characteristics

 $T_{amb} = 25$ °C unless otherwise specified.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I _{CBO}	collector-base cut-off current	$V_{CB} = -50 \text{ V}; I_E = 0 \text{ A}$	-	-	-100	nA
I _{CEO}	collector-emitter	$V_{CE} = -30 \text{ V}; I_{B} = 0 \text{ A}$	-	-	-1	μΑ
•	cut-off current	$V_{CE} = -30 \text{ V}; I_{B} = 0 \text{ A};$ $T_{j} = 150 ^{\circ}\text{C}$	-	-	-5	μΑ
I _{EBO}	emitter-base cut-off current	$V_{EB} = -5 \text{ V}; I_C = 0 \text{ A}$	-	-	-90	μΑ
h _{FE}	DC current gain	$V_{CE} = -5 \text{ V}; I_{C} = -5 \text{ mA}$	80	-	-	
V _{CEsat}	collector-emitter saturation voltage	$I_C = -10 \text{ mA}; I_B = -0.5 \text{ mA}$	-	-	-150	mV
$V_{I(off)}$	off-state input voltage	$V_{CE} = -5 \text{ V}; I_{C} = -100 \mu\text{A}$	-	-1.2	-0.8	V
$V_{I(on)}$	on-state input voltage	$V_{CE} = -0.3 \text{ V}; I_{C} = -2 \text{ mA}$	-3	-1.6	-	V
R1	bias resistor 1 (input)		33	47	61	kΩ
R2/R1	bias resistor ratio		0.8	1	1.2	
C _c	collector capacitance	$V_{CB} = -10 \text{ V}; I_E = i_e = 0 \text{ A};$ f = 1 MHz	-	-	3	pF
f _T	transition frequency	$V_{CE} = -5 \text{ V}; I_{C} = -10 \text{ mA};$ [1] $f = 100 \text{ MHz}$	-	180	-	MHz

^[1] Characteristics of built-in transistor



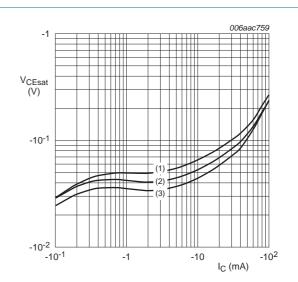
$$V_{CE} = -5 \text{ V}$$

(1)
$$T_{amb} = 100 \, ^{\circ}C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(3) $T_{amb} = -40 \, ^{\circ}C$

Fig 6. DC current gain as a function of collector current; typical values



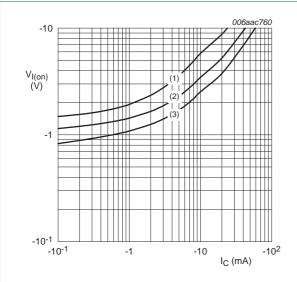
$$I_{\rm C}/I_{\rm B} = 20$$

(1)
$$T_{amb} = 100 \, ^{\circ}C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(3)
$$T_{amb} = -40 \, ^{\circ}C$$

Fig 7. Collector-emitter saturation voltage as a function of collector current; typical values



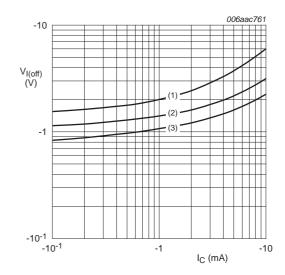
$$V_{CE} = -0.3 \text{ V}$$

(1)
$$T_{amb} = -40 \, ^{\circ}C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(3) $T_{amb} = 100 \, ^{\circ}C$

Fig 8. On-state input voltage as a function of collector current; typical values



$$V_{CE} = -5 \text{ V}$$

(1)
$$T_{amb} = -40 \, ^{\circ}C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(3) $T_{amb} = 100 \, ^{\circ}C$

Fig 9. Off-state input voltage as a function of collector current; typical values

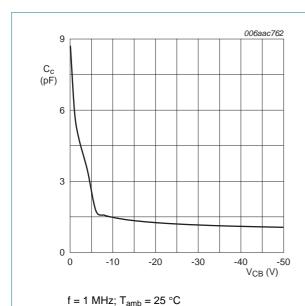


Fig 10. Collector capacitance as a function of collector-base voltage; typical values of built-in transistor

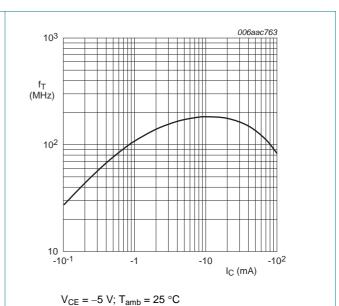


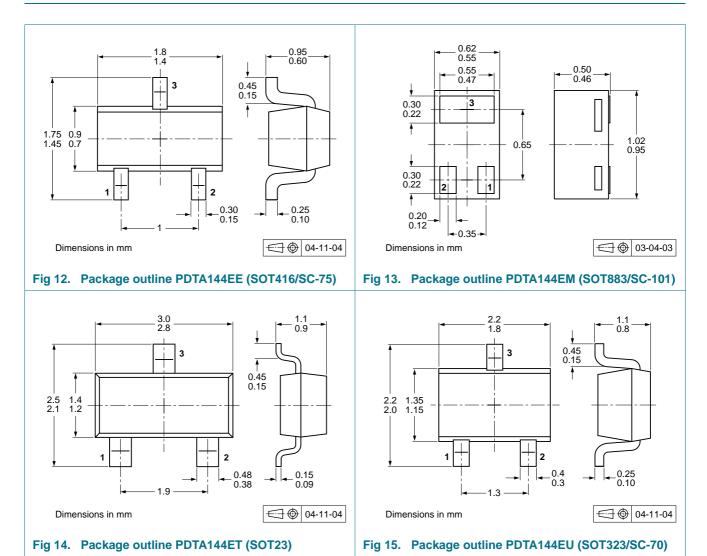
Fig 11. Transition frequency as a function of collector current; typical values of built-in transistor

8. Test information

8.1 Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101 - Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

9. Package outline



10. Packing information

Table 9. Packing methods

The indicated -xxx are the last three digits of the 12NC ordering code.[1]

Type number	Package	Description	Packing	Packing quantity			
			3000	5000	10000		
PDTA144EE	SOT416	4 mm pitch, 8 mm tape and reel	-115	-	-135		
PDTA144EM	SOT883	2 mm pitch, 8 mm tape and reel	-	-	-315		
PDTA144ET	SOT23	4 mm pitch, 8 mm tape and reel	-215	-	-235		
PDTA144EU	SOT323	4 mm pitch, 8 mm tape and reel	-115	-	-135		

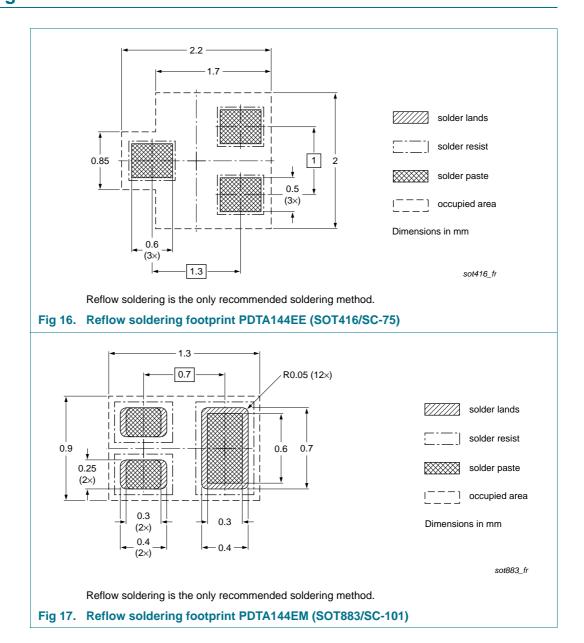
[1] For further information and the availability of packing methods, see Section 14.

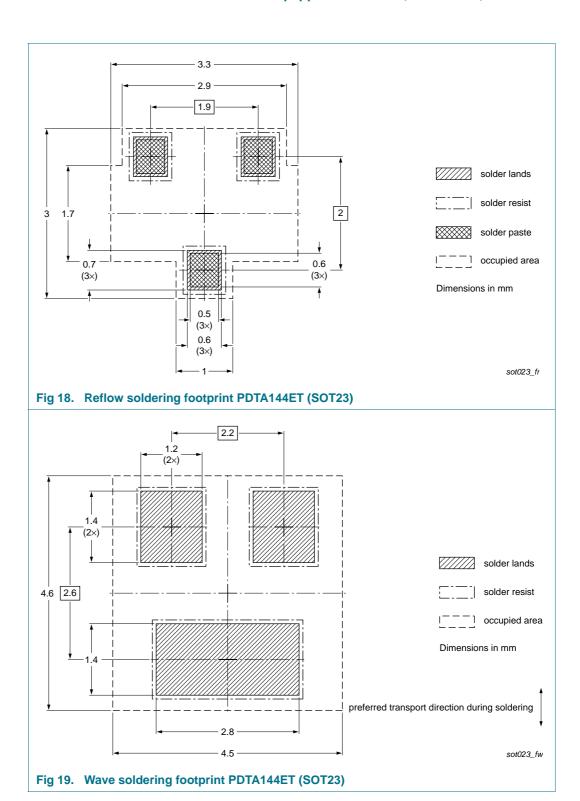
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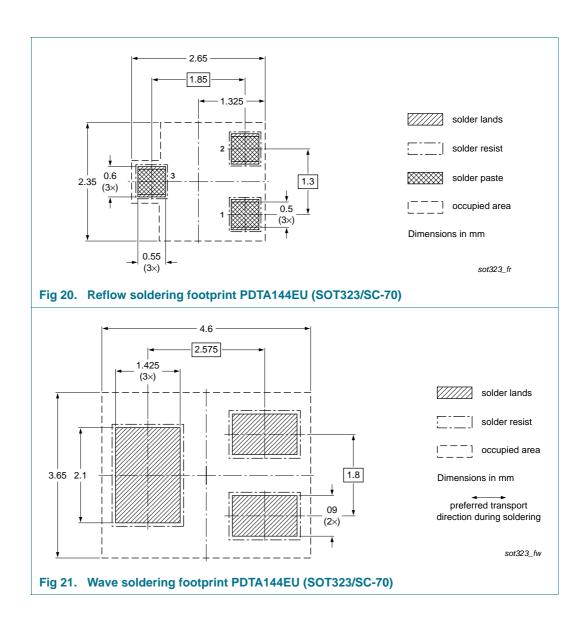
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11. Soldering







12. Revision history

Table 10. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
PDTA144E_SERIES v.8	20111114	Product data sheet	-	PDTA144E_SERIES v.7
Modifications:	 The format of guidelines of Legal texts head to Example of Section 1 "Properties" Section 4 "Modern of the Example of	of this document has been referred to the new part of this document has been referred to the new part of the part	ew company name whe EK and PDTA144ES redated do $V_{I(on)}$ on-state input lated, f_T added do by minimized packaged	ith the new identity re appropriate. moved. voltage, V _{i(off)} redefined
PDTA144E_SERIES v.7	20040805	Product data sheet	-	PDTA144E_SERIES v.6
PDTA144E_SERIES v.6	20030410	Product specification	-	-

13. Legal information

13.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design
- [2] The term 'short data sheet' is explained in section "Definitions"
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PDTA144E series

PNP resistor-equipped transistors; R1 = 47 k Ω , R2 = 47 k Ω

Quick reference data — The Quick reference data is an extract of the product data given in the Limiting values and Characteristics sections of this document, and as such is not complete, exhaustive or legally binding.

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PDTA144E series

PNP resistor-equipped transistors; R1 = 47 k Ω , R2 = 47 k Ω

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